Abstracts

Low-frequency noise and phase noise behavior of advanced SiGe HBTs

L. Bary, G. Cibiel, J. Ibarra, O. Llopis, R. Plana, J. Graffeuil, G. Niu, J.D. Cressler, Z. Jin, S. Zhang and A.J. Joseph. "Low-frequency noise and phase noise behavior of advanced SiGe HBTs." 2001 MTT-S International Microwave Symposium Digest 01.3 (2001 Vol. III [MWSYM]): 1705-1708 vol.3.

This paper addresses low frequency noise and residual phase noise in advanced SiGe HBTs featuring different Ge profile shape. Under certain bias conditions, increasing the Ge content decreases the base current fluctuations and hence improves the residual phase noise performance. Additional low frequency noise and phase noise measurements have provided a better insight into the physical location of the 1/f noise sources in these devices.

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